NIPPON SANSO

UR26K-CCD

UR Series for GaN in Multiple Types of 150/200 mm Production Reactors

Large scale deposition system.



World's First Fully Automated MOCVD Platform

Lowest Achievable Cost of Ownership with High Throughput Reactor and Integrated Dry Cleaning Technology



Integration of dry cleaning system



Cassette-to-Cassette System

Fully automated cassette-to-cassette (CtoC) wafer loading increases throughput, reduces contamination from wafer handling, and increases overall product yield.

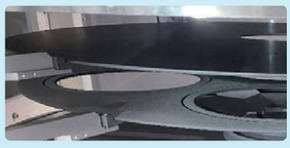
Integrated Dry Cleaning System

Maximizes the productivity of the MOCVD.
High cleaning performance that maintains condition of reactor components results in constant perfect growth conditions.

UR26K-CCD Specifications

Wafer size	8” x 6 or 6” x 10
Reactor type	Rotation/revolution
Wafer face	Face up
Rotation/revolution mechanism	Mechanical/mechanical (for stable revolution/rotation motion)
Gas flow	Three laminar flow horizontals
Growth pressure	Low to atmospheric pressure High flow velocity narrow channel
Heating system	6 zone resistance heaters

Before and after cleaning

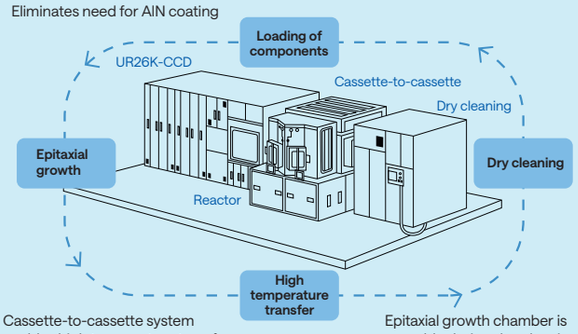


Before cleaning

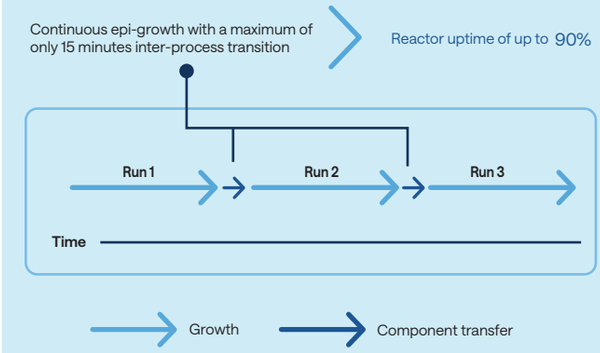


After cleaning

Concept of UR26K-CCD



Reactor operation



Visit Our Website & YouTube Channel

https://nsc.jp.nipponsanso.com/mocvd/

https://www.youtube.com/watch?v=iyMkq5xpfUg

https://www.youtube.com/watch?v=_OUGapoN16U

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Address: 1-3-26 Koyama, Shinagawa-ku, Tokyo 142-8558, Japan
E-mail: mocvd@jp.nipponsanso.com
TEL: (81) 03-3457-9220

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